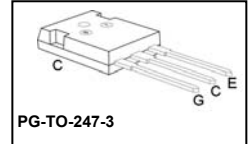
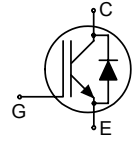


TrenchStop® Reverse Conducting (RC-)IGBT with monolithic body diode

Features:

- Powerful monolithic Body Diode with very low forward voltage
- Body diode clamps negative voltages
- Trench and Fieldstop technology for 1600 V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Applications:

- Inductive Cooking
- Soft Switching Applications

Type	V_{CE}	I_C	$V_{CE(sat)}, T_J=25^\circ\text{C}$	$T_{j,max}$	Marking	Package
IHW30N160R2	1600V	30A	1.8V	175°C	H30R1602	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1600	V
DC collector current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_C	60 30	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	90	
Turn off safe operating area ($V_{CE} \leq 1600\text{V}$, $T_J \leq 175^\circ\text{C}$)	-	90	
Diode forward current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_F	60 30	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	90	
Diode surge non repetitive current, t_p limited by T_{jmax} $T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$, sine halfwave $T_C = 25^\circ\text{C}$, $t_p \leq 2.5\mu\text{s}$, sine halfwave $T_C = 100^\circ\text{C}$, $t_p \leq 2.5\mu\text{s}$, sine halfwave	I_{FSM}	50 130 120	V
Gate-emitter voltage	V_{GE}	± 20	
Transient Gate-emitter voltage ($t_p < 10 \mu\text{s}$, $D < 0.01$)		± 25	
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	312	W
Operating junction temperature	T_J	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ J-STD-020 and JESD-022

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.48	K/W
Diode thermal resistance, junction – case	R_{thJCD}		0.48	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	1600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=30A$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$ $T_j=175^{\circ}C$	- - -	1.8 2.25 2.35	2.1 - -	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=30A$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$ $T_j=175^{\circ}C$	- - -	1.65 2.0 2.0	2.0 - -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.75mA,$ $V_{CE}=V_{GE}$	5.1	5.8	6.4	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1600V,$ $V_{GE}=0V$ $T_j=25^{\circ}C$ $T_j=175^{\circ}C$	- -	- -	5 2500	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=30A$	-	22.5	-	S
Integrated gate resistor	R_{Gint}			none		Ω

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	2740	-	pF
Output capacitance	C_{oss}		-	68.1	-	
Reverse transfer capacitance	C_{rss}		-	58.7	-	
Gate charge	Q_{Gate}	$V_{CC}=1280V,$ $I_C=30A; V_{GE}=15V$	-	94	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH

Switching Characteristic, Inductive Load, at $T_j=25^\circ C$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-off delay time	$t_{d(off)}$	$T_j=25^{\circ}C$, $V_{CC}=600V, I_C=30A$ $V_{GE}=0 / 15V$, $R_G=10\Omega$	-	525	-	ns
Fall time	t_f		-	38.3	-	
Turn-on energy	E_{on}		-	-	-	
Turn-off energy	E_{off}		-	2.53	-	mJ
Total switching energy	E_{ts}		-	2.53	-	

Switching Characteristic, Inductive Load, at $T_j=175^\circ C$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-off delay time	$t_{d(off)}$	$T_j=175^{\circ}C$ $V_{CC}=600V, I_C=30A,$ $V_{GE}= 0 / 15V,$ $R_G= 10\Omega$	-	564	-	ns
Fall time	t_f		-	111	-	
Turn-on energy	E_{on}		-	-	-	
Turn-off energy	E_{off}		-	4.37	-	mJ
Total switching energy	E_{ts}		-	4.37	-	

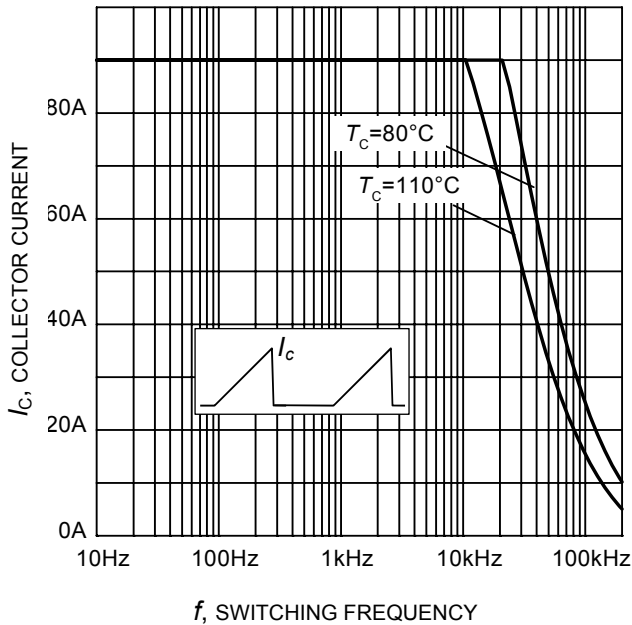


Figure 1. Collector current as a function of switching frequency for hard switching (turn-off)

($T_j \leq 175^\circ\text{C}$, $D = 0.5$, $V_{CE} = 600\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 10\Omega$)

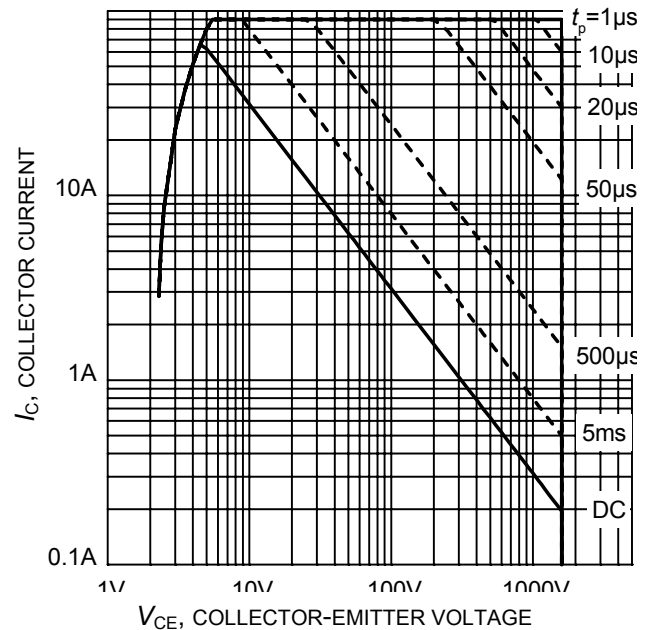


Figure 2. IGBT Safe operating area

($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$)

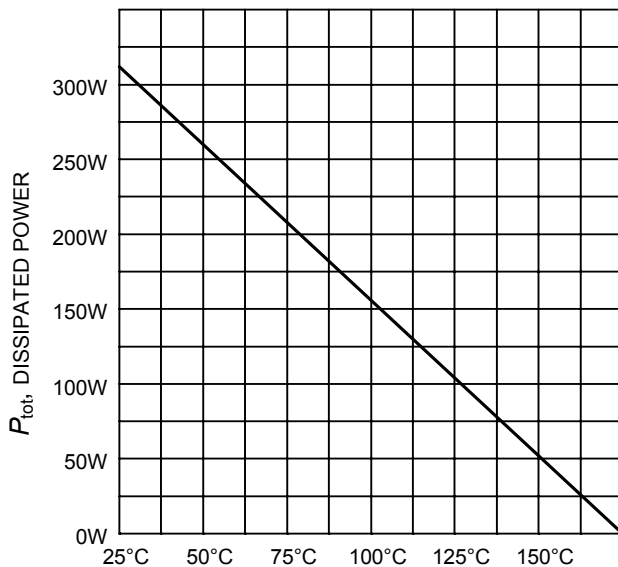


Figure 3. Power dissipation as a function of case temperature

($T_j \leq 175^\circ\text{C}$)

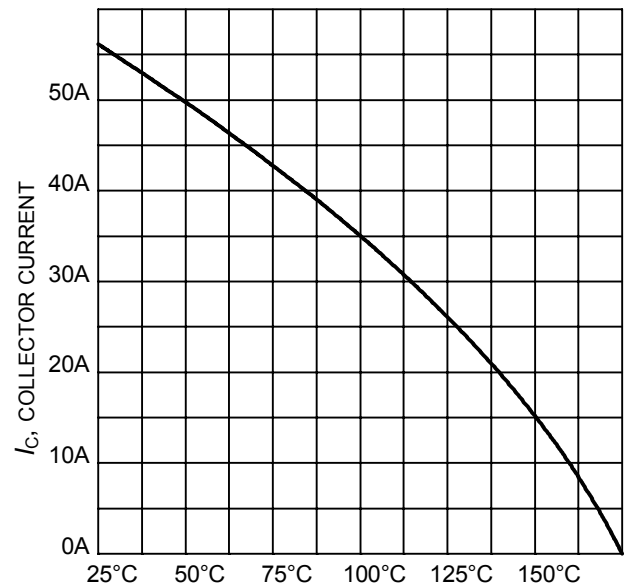


Figure 4. DC Collector current as a function of case temperature

($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

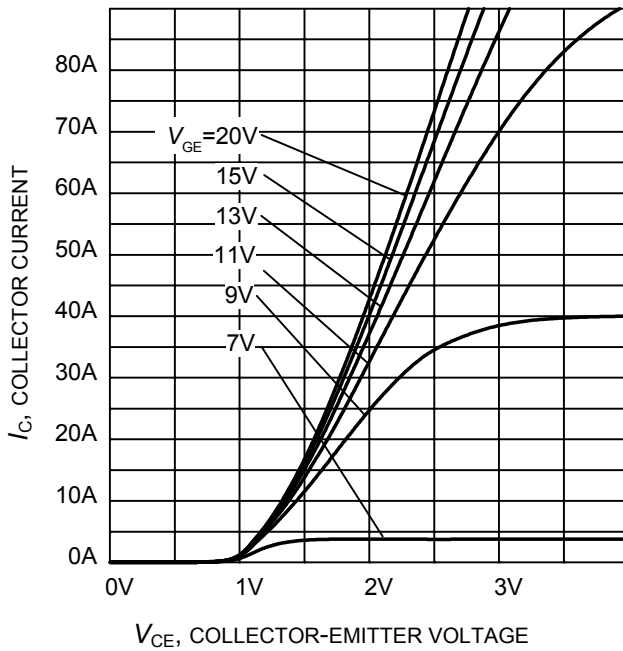


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

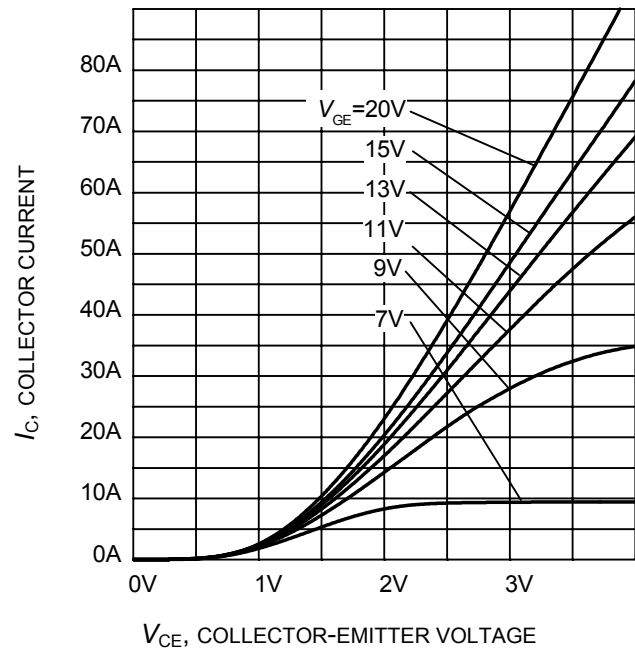


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

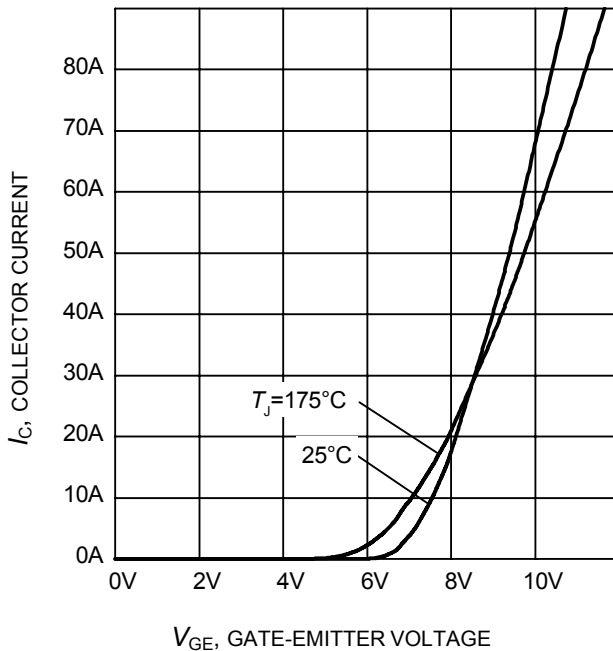


Figure 7. Typical transfer characteristic
($V_{ce} = 20\text{V}$)

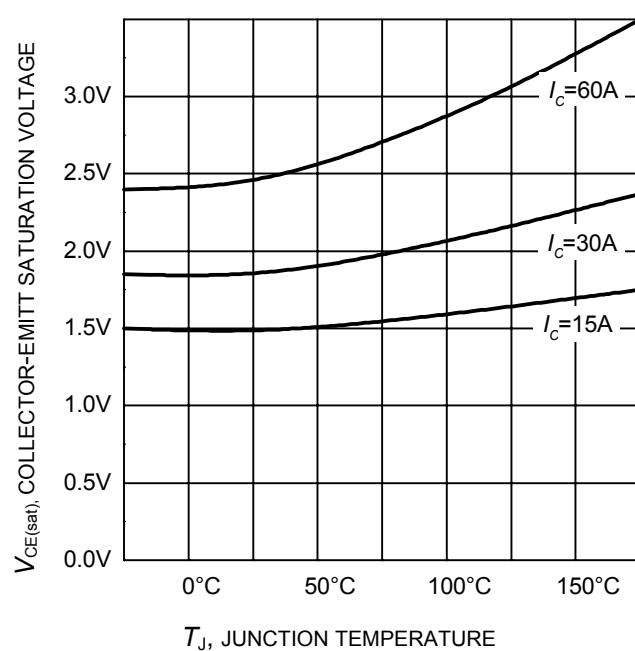


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{ge} = 15\text{V}$)

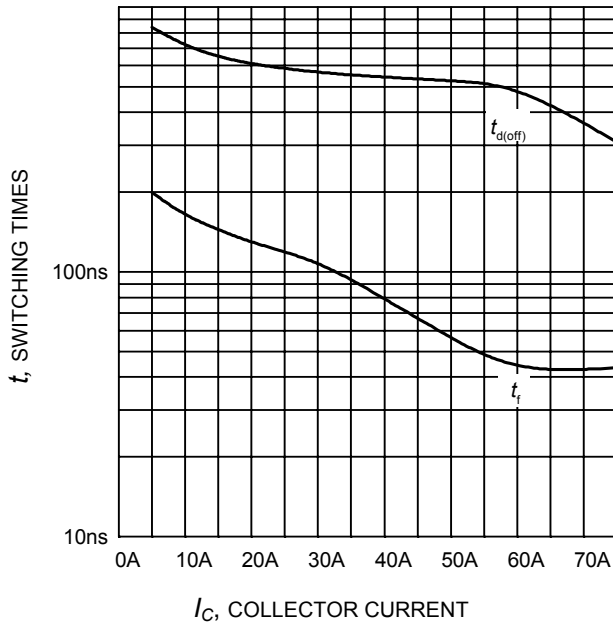


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=10\Omega$, Dynamic test circuit in Figure E)

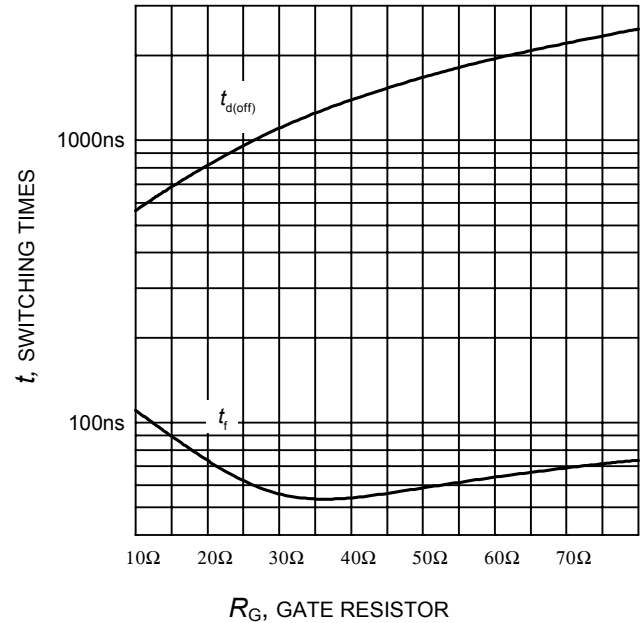


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

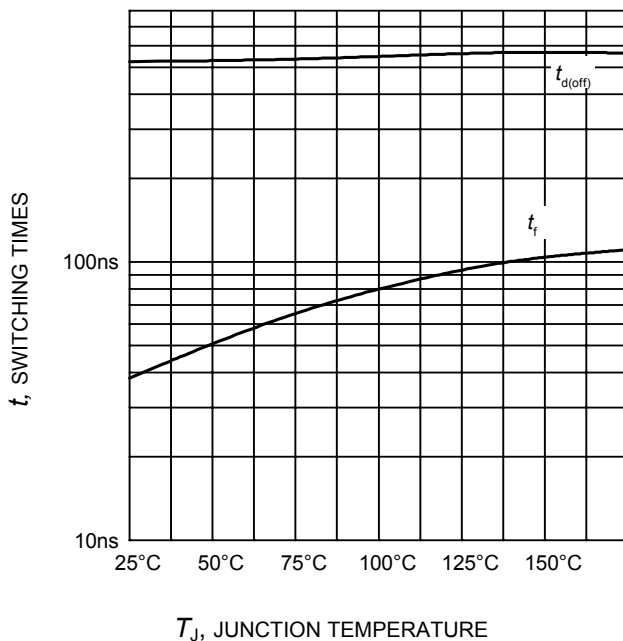


Figure 11. Typical switching times as a function of junction temperature
(inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=10\Omega$, Dynamic test circuit in Figure E)

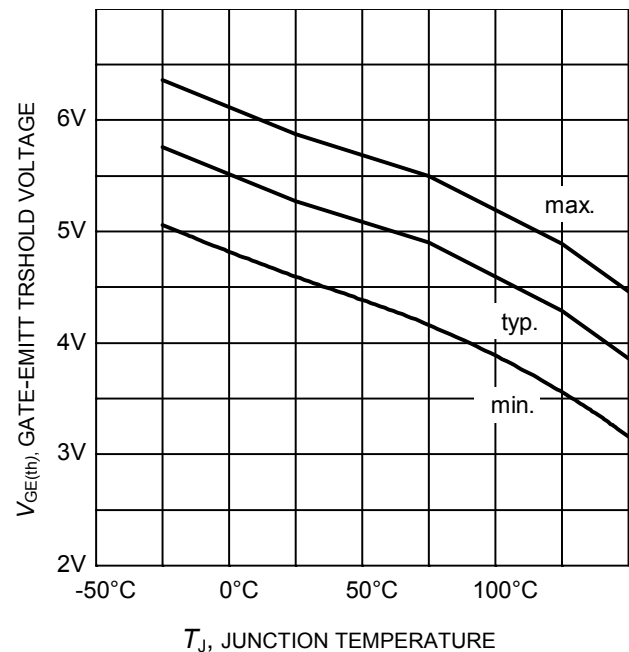


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 0.15\text{mA}$)

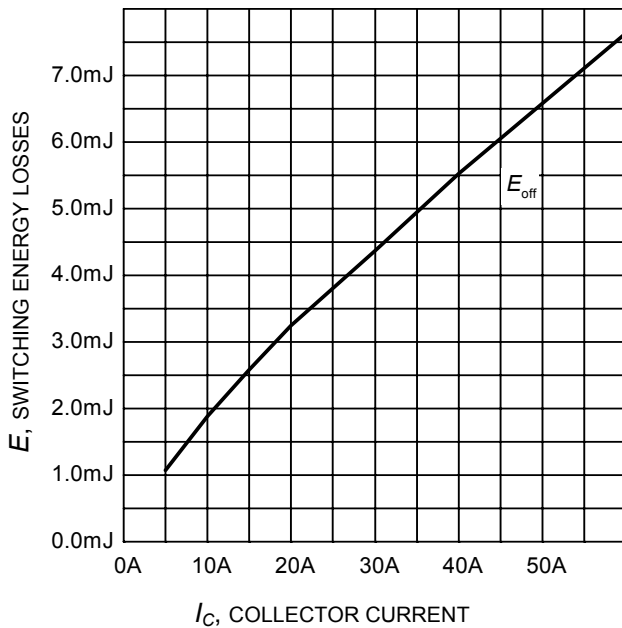


Figure 13. Typical turn-off energy as a function of collector current
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=10\Omega$, Dynamic test circuit in Figure E)

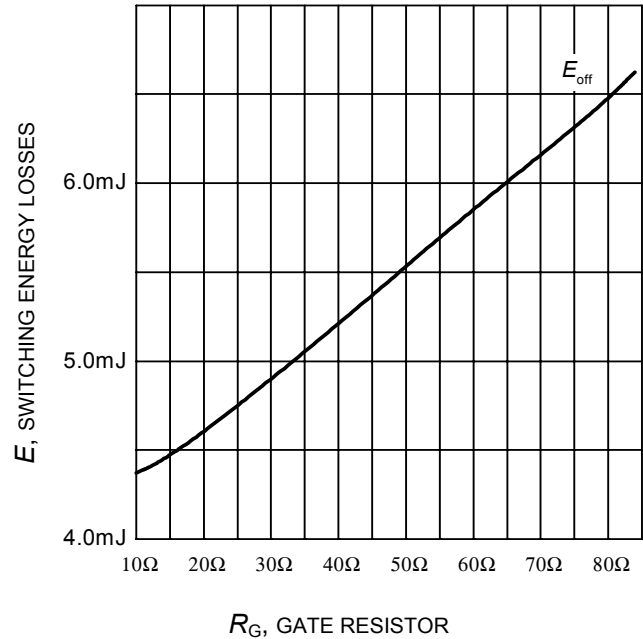


Figure 14. Typical turn-off energy as a function of gate resistor
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

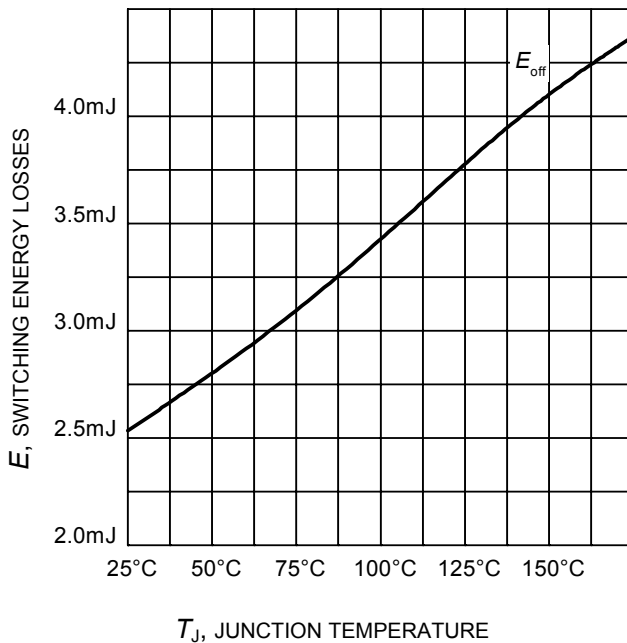


Figure 15. Typical turn-off energy as a function of junction temperature
(inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=10\Omega$, Dynamic test circuit in Figure E)

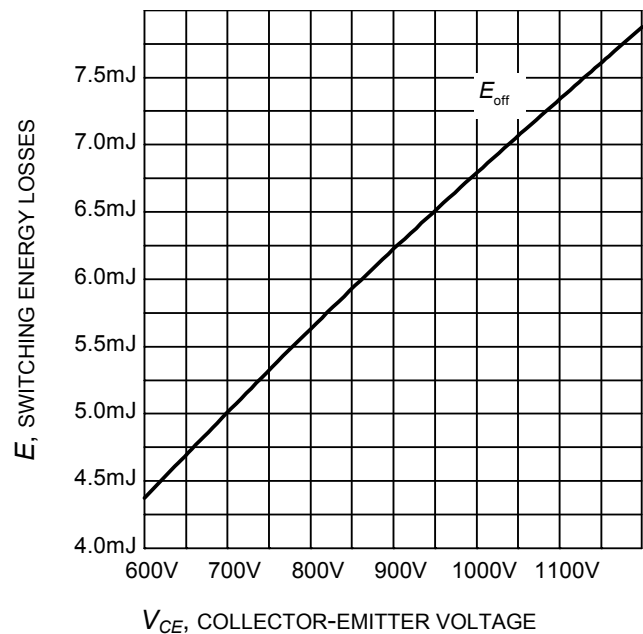


Figure 16. Typical turn-off energy as a function of collector emitter voltage
(inductive load, $T_J=175^\circ\text{C}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=10\Omega$, Dynamic test circuit in Figure E)

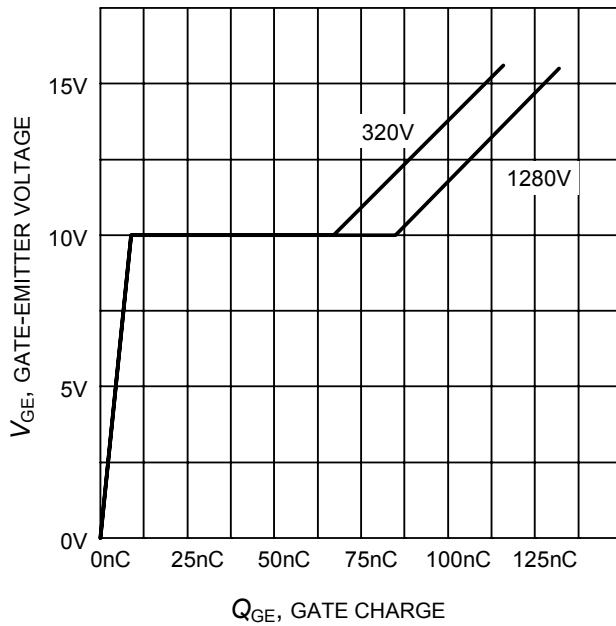


Figure 17. Typical gate charge
($I_C = 30\text{ A}$)

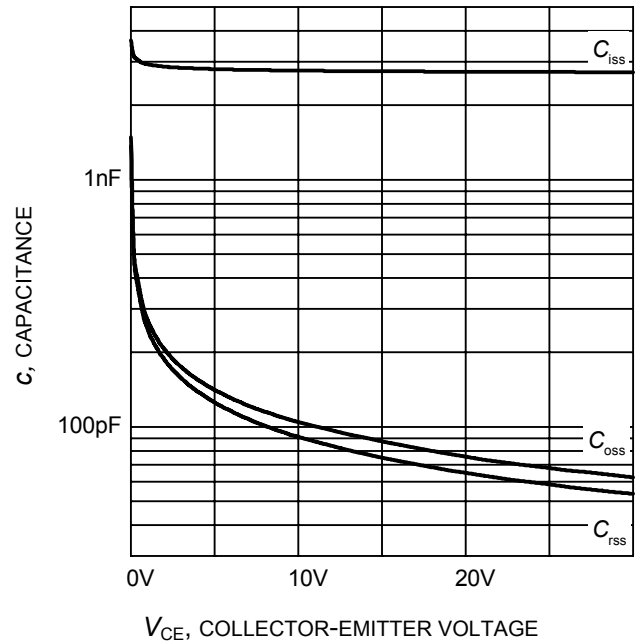


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$)

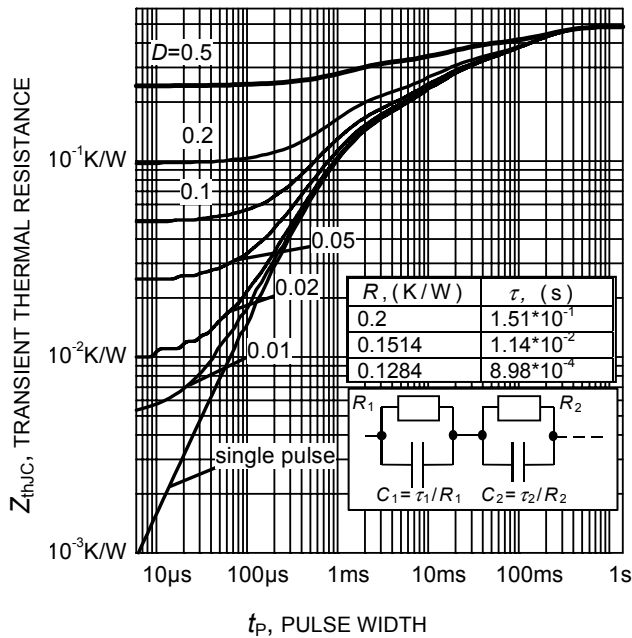


Figure 19. IGBT transient thermal resistance
($D = t_p / T$)

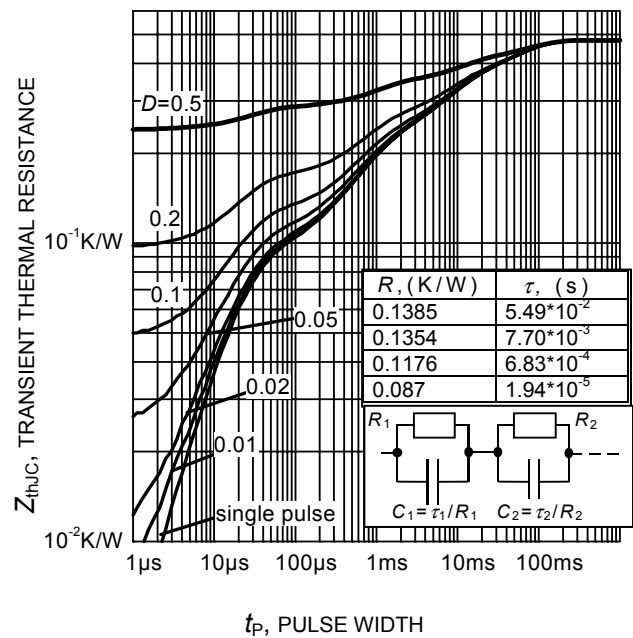


Figure 20. Diode transient thermal impedance as a function of pulse width
($D = t_p / T$)

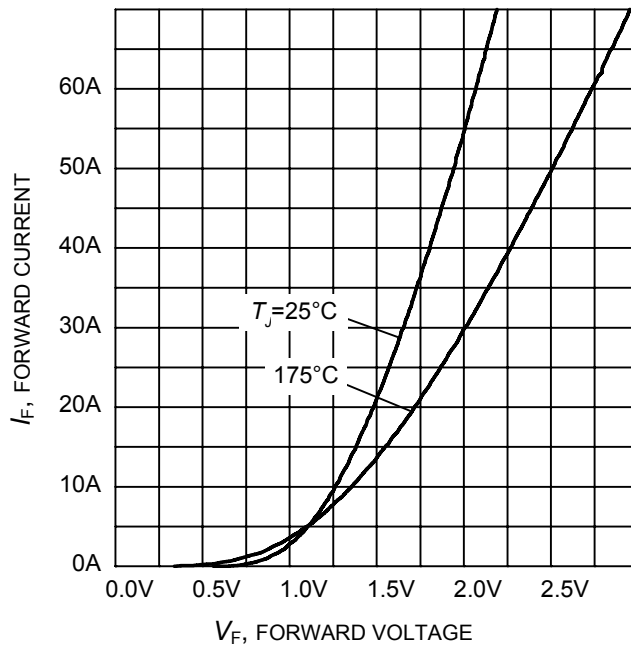


Figure 21. Typical diode forward current as a function of forward voltage

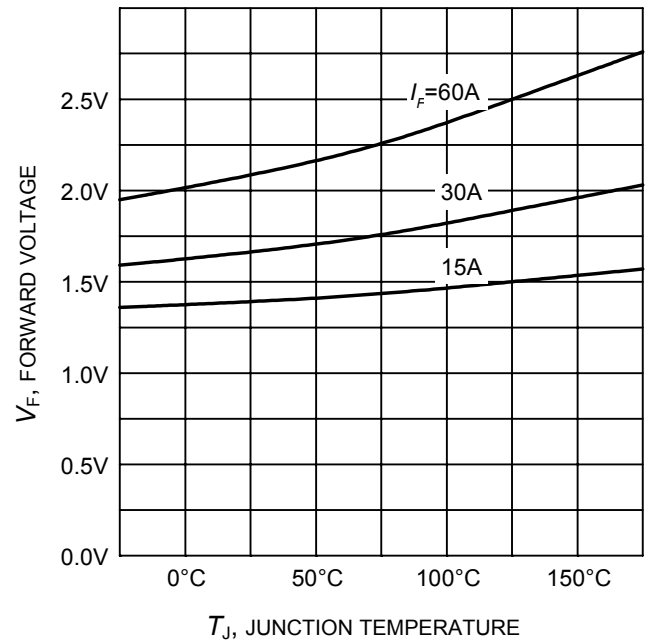
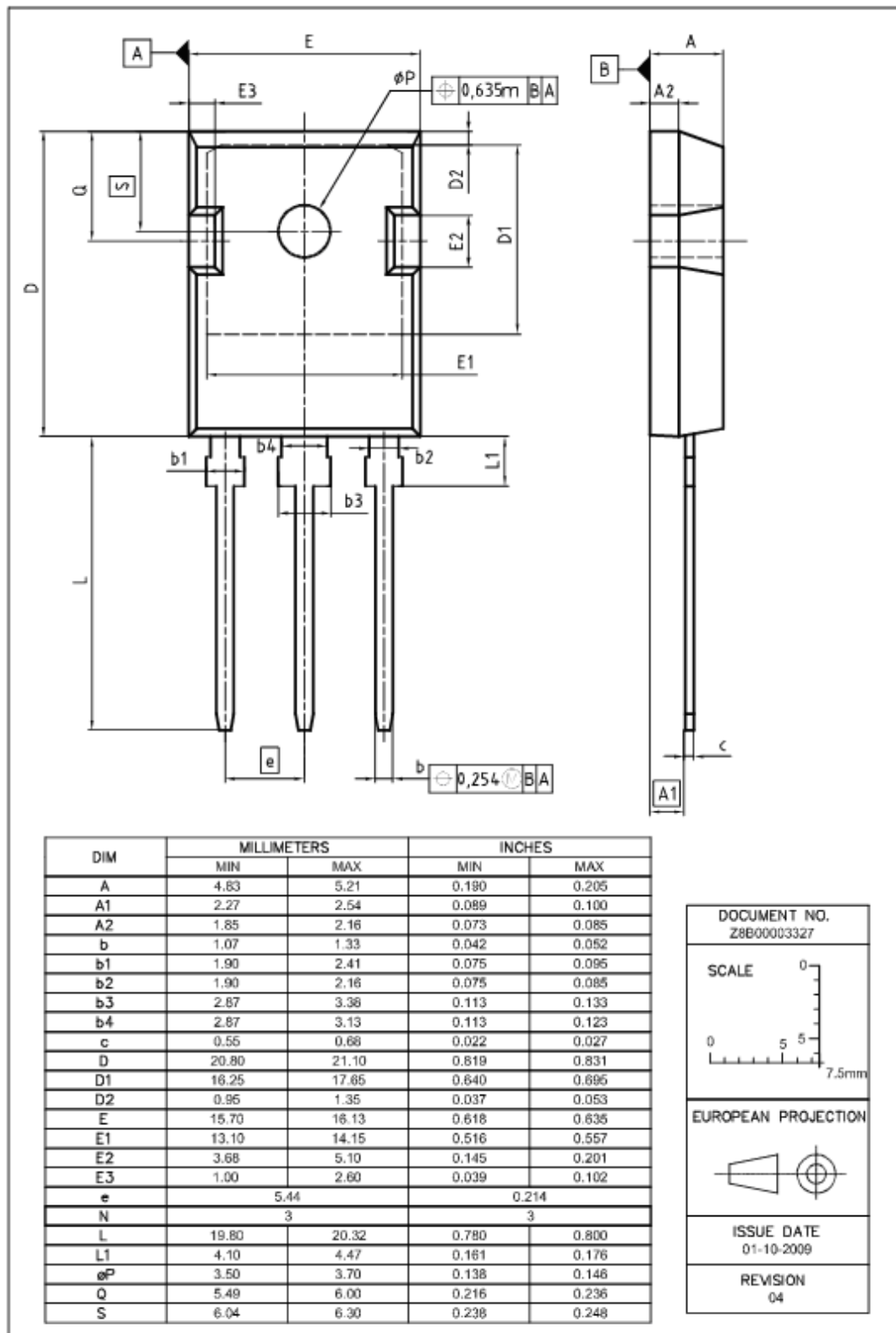


Figure 22. Typical diode forward voltage as a function of junction temperature

TO247-3



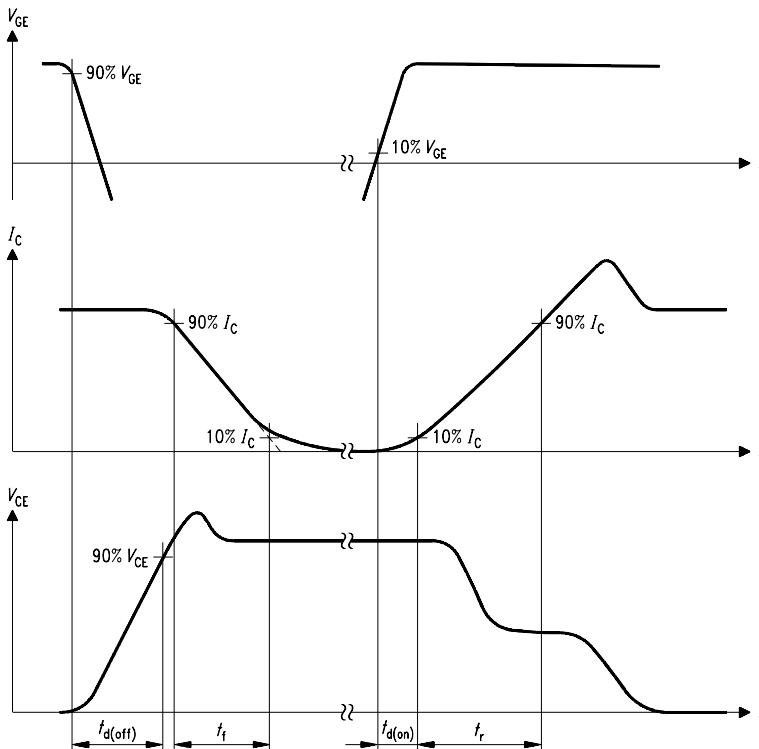


Figure A. Definition of switching times

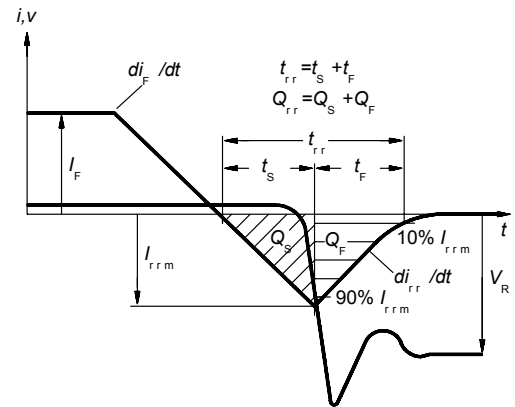


Figure C. Definition of diodes switching characteristics

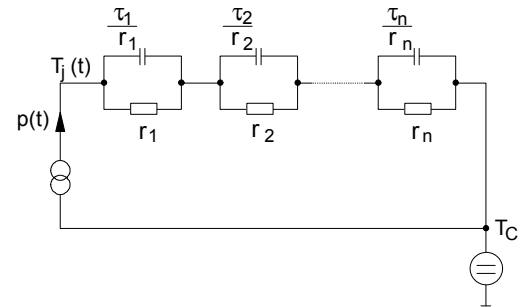


Figure D. Thermal equivalent circuit

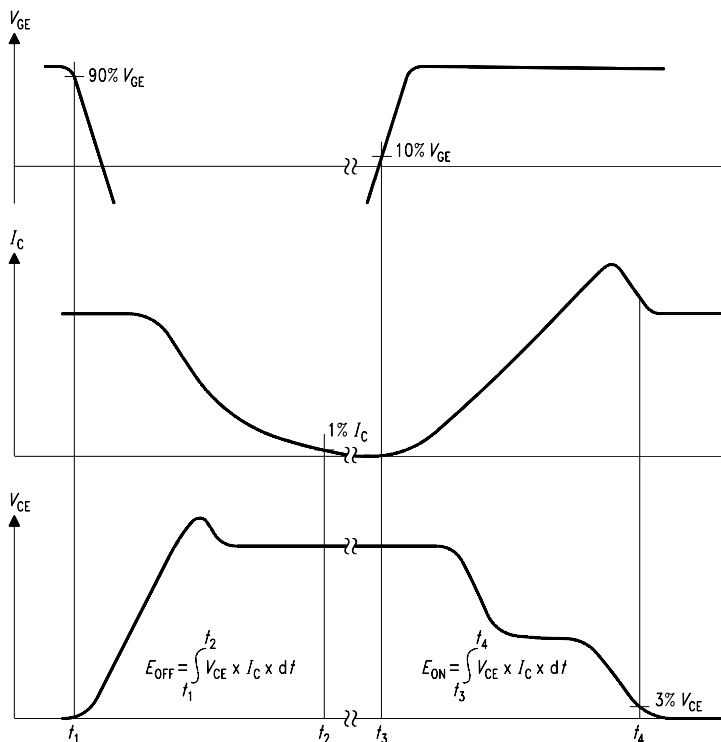


Figure B. Definition of switching losses

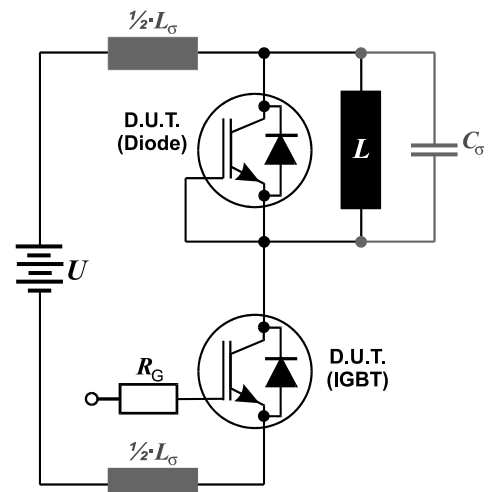


Figure E. Dynamic test circuit

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